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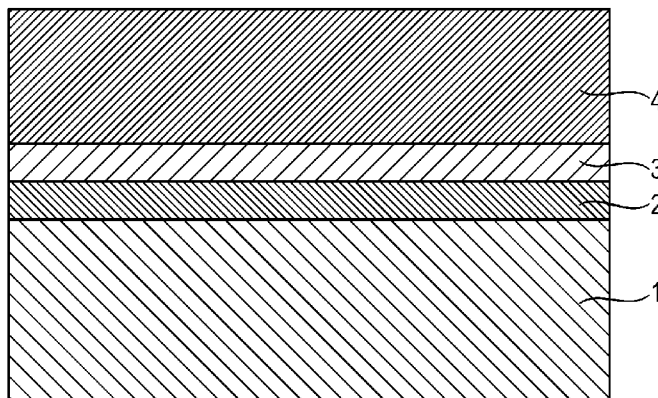
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(54) **Title:** LAYERED SEMICONDUCTOR SUBSTRATE AND METHOD FOR MANUFACTURING IT**Fig. 3**

(57) **Abstract:** The invention relates to a layered semiconductor substrate comprising - a monocrystalline first layer (1) containing at least 80 % silicon and having a first thickness and a first lattice constant a_1 , the first lattice constant a_1 being determined by a first dopant element and a first dopant concentration and - a monocrystalline second layer (2) containing at least 80 % silicon and having a second thickness and a second lattice constant a_2 , the second lattice constant a_2 being determined by a second dopant element and a second dopant concentration, the second layer (2) being in direct contact with the first layer, and - a monocrystalline third layer (4) comprising a group III nitride, such that the second layer is located between the first layer and the third layer, wherein the second lattice constant is larger than the first lattice constant, wherein the crystal lattice of the first layer (1) and the second layer (2) are lattice-matched and wherein the bow of the layered semiconductor substrate is in the range from $-50\text{ }\mu\text{m}$ to $50\text{ }\mu\text{m}$. The invention also relates to a method for manufacturing this layered semiconductor substrate.